

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	1.5Ω@10V	0.22A
	1.8Ω@4.5V	

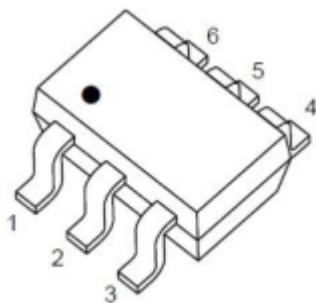
Feature

- Energy Efficient
- Low Threshold Voltage
- High-speed Switching
- Miniature Surface Mount Package Saves Board Space
- ESD Protected

Applications

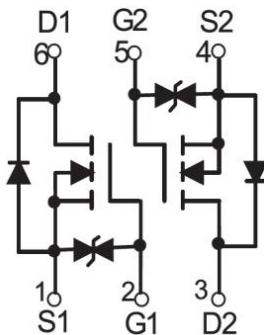
- DC-DC converters
- load switching
- power management in portable
- battery-powered products

Package

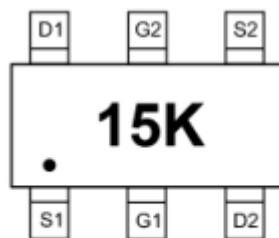


SOT-363

Circuit diagram



Marking



15K =Device Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	0.22	A
Plused Drain Current ⁽¹⁾ @ $t_p < 10\mu\text{s}$	I_{DM}	0.88	A
Power Dissipation	P_D	320	W
Thermal Resistance from Junction to Ambient ⁽²⁾	$R_{\theta JA}$	390	$^\circ\text{C} / \text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$



ZL MOSFET

ZL60N15KA

Electrical characteristics

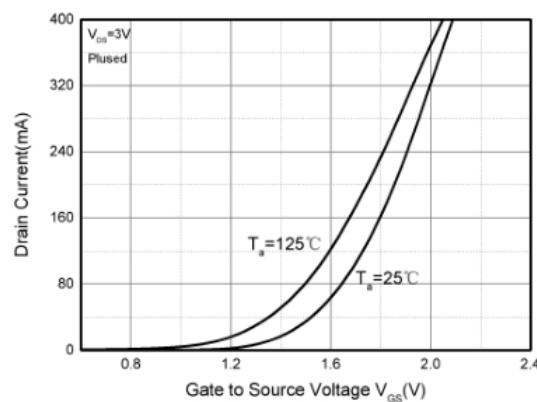
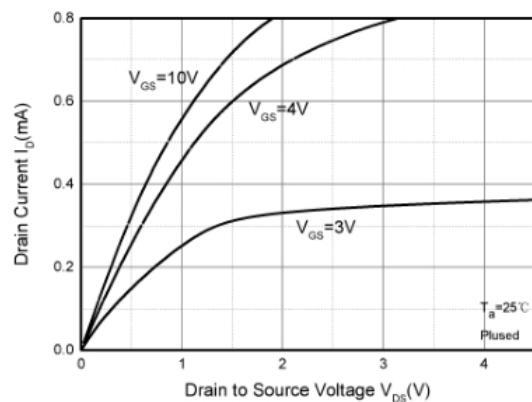
(T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV (BR)DSS	V _{GS} = 0V, I _D = 250μA	60			V
Drain Leakage Current	I _{DSS}	V _{DS} = 48V, V _{GS} = 0V			1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±10	uA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.7	1.0	1.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 200mA		1.5	3.5	mΩ
		V _{GS} = 4.5V, I _D = 200mA		1.8	5	
		V _{GS} = 2.5V, I _D = 100mA		2.5	8	
		V _{GS} = 1.8V, I _D = 10mA		4.5	10	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		27		pF
Output Capacitance	C _{oss}			13		
Reverse Transfer Capacitance	C _{rss}			6		
Switching Characteristics						
Turn-On Delay Time	T _{d(on)}	V _{DD} = 30V, I _D = 300mA, V _{GS} = 10V, R _G = 6Ω		2.5		nS
Rise Time	T _r			18		
Turn-Off Delay Time	T _{d(off)}			9.7		
Fall Time	T _f			48		
Diode Characteristics						
Diode Forward Voltage ²	V _{SD}	V _{GS} = 0V, I _S = 0.5A			1.2	V

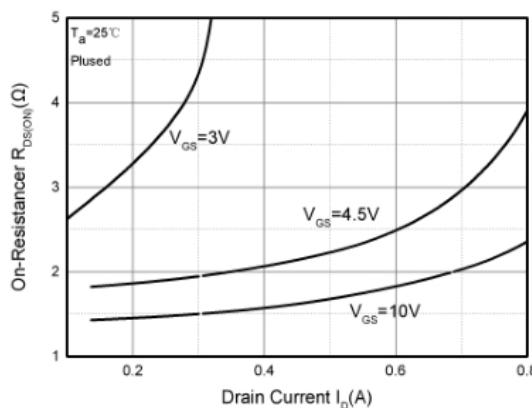
Note :

1. Repetitive rating: Pulse width limited by junction temperature.
2. Surface mounted on FR4 board, t ≤ 10s.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production.

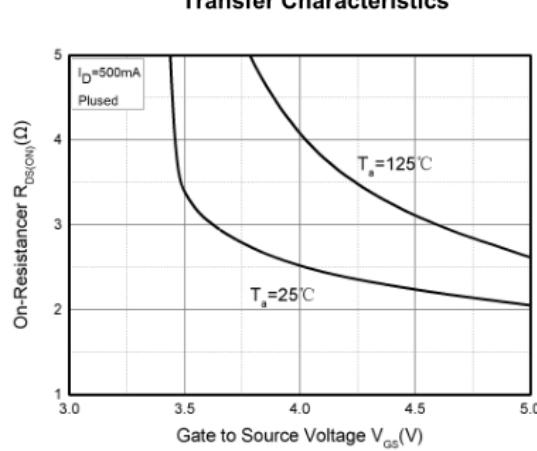
Typical Characteristics



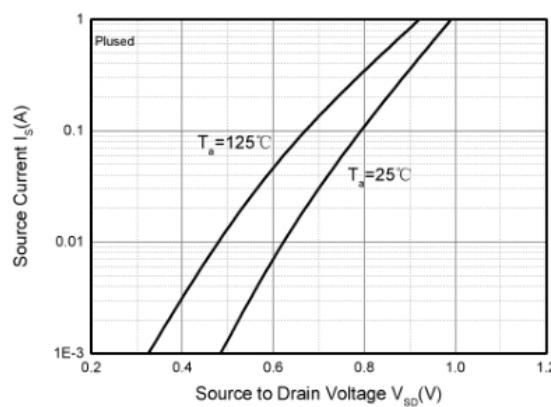
Output Characteristics



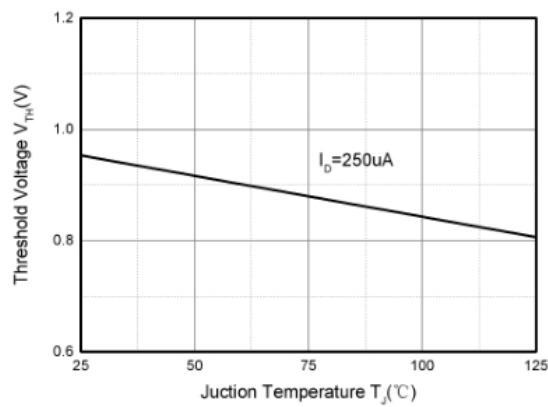
RDS(ON)——ID



RDS(ON)——VGS

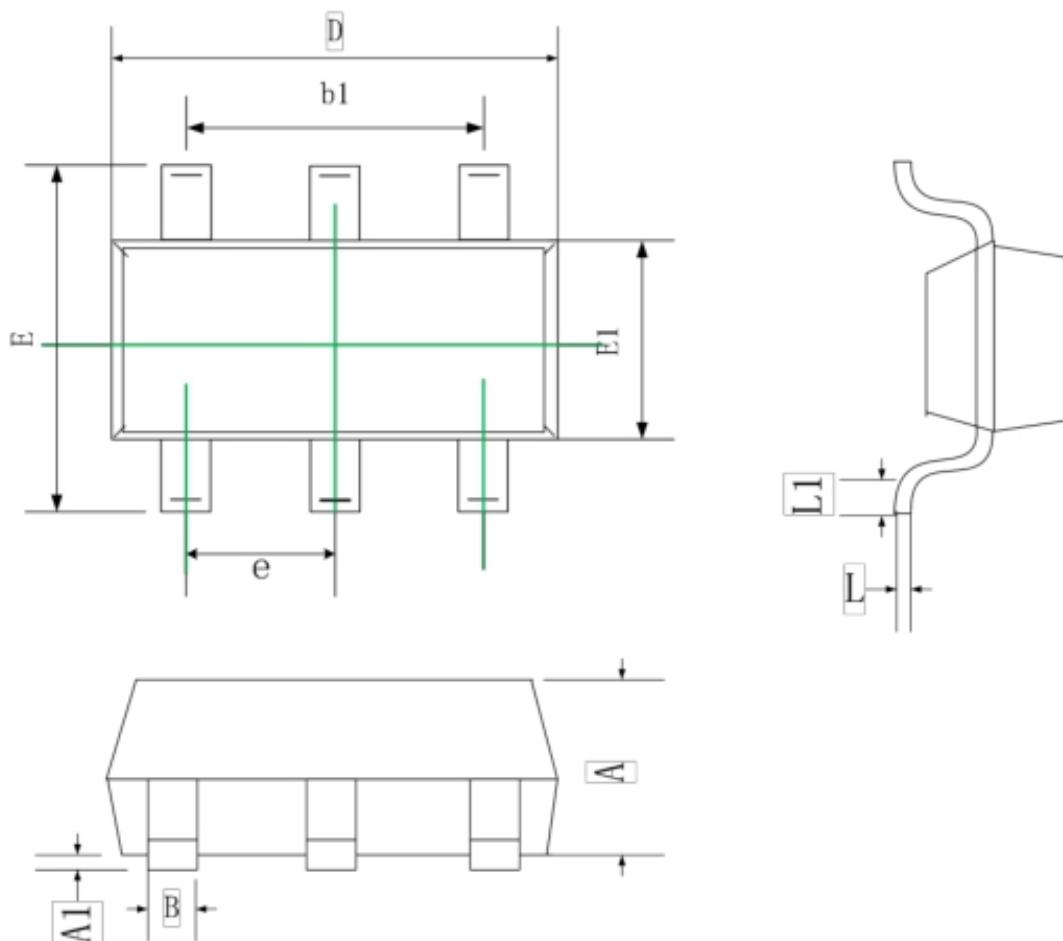


IS——VSD



Threshold Voltage

SOT-363 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.00
A1	0.00	0.10
B	0.10	0.30
b1	1.30	
D	1.80	2.20
E	2.00	2.20
E1	1.15	1.35
e	0.65 TYP.	
L	0.10	0.25
L1	0.15	0.4